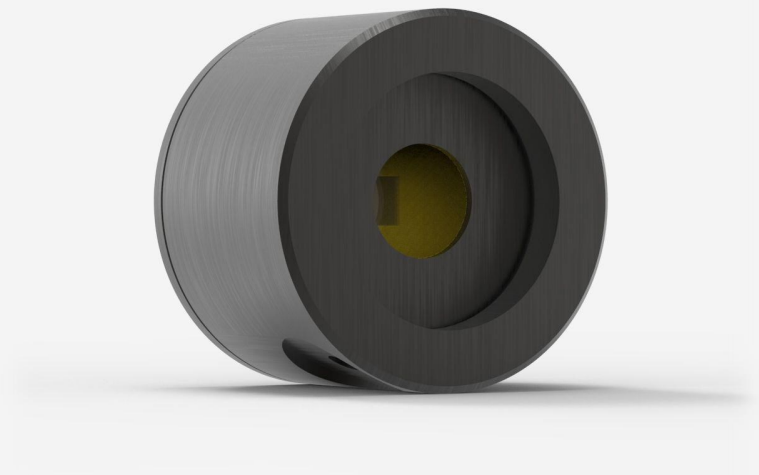
PH20-GE-D0

Photodiode detector for laser power measurement up to 30 mW.



PRODUCT FAMILY KEY FEATURES

LARGE APERTURES

10 mm Ø for the silicon sensors

3 VERSIONS

- Silicon 350 - 1080 nm, up to 750 mW
- Silicon-UV 210 - 1080 nm, up to 38 mW
- Germanium 800 - 1650 nm, up to 500 mW

CHOICE OF ATTENUATORS

Models with attenuators include a calibration both with and without the removable filter

HIGH ACCURACY

The new PH100-SI-HA presents the lowest calibration uncertainty to date.

PRECISE CALIBRATION

Wavelength selection in 1 nm steps

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

MEASUREMENT CAPABILITIES

Maximum average power[1]	30 mW
Noise equivalent power[2]	60 pW
Spectral range	800 - 1650 nm
Typical rise time	0.2 s
Power calibration uncertainty	±5.0 % (800 - 1049 nm) ±3.5 % (1050 - 1559 nm) ±7.0 % (1560 - 1629 nm) ±10 % (1630 - 1650 nm)
Peak sensitivity	0.98 A/W @ 1550 nm
Minimum repetition rate[3]	155 kHz

1. At 1064 nm. See curves for maximum power at other wavelengths.
2. At 1550 nm. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength.
3. See user manual for details.

DAMAGE THRESHOLDS

Maximum average power density	100 W/cm²

PHYSICAL CHARACTERISTICS

Aperture diameter	5 mm
Absorber	Ge
Dimensions	38.1Ø x 27.4D mm
Weight	0.13 kg
Distance to sensor face	10.5 mm

ORDERING INFORMATION

PH20-Ge-D0	200866
PH20-Ge-IDR-D0	203242

Specifications are subject to change without notice. Refer to the user manual for complete specifications.

INTERESTED IN THIS PRODUCT?

GET A QUOTE

Find your local sales representative at gentec-eo.com/contact-us